# 2SD1295

### Silicon NPN epitaxial planar type

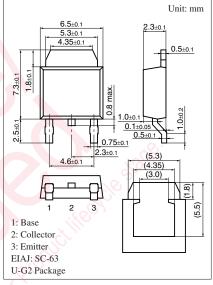
For low-frequency output amplification Complementary to 2SB0968

#### Features

- Possible to solder radiation fin directly to printed circuit board
- Output of 4 W can be obtained by a complementary pair with 2SB0968

Absolute Maximum Ratings $T_c = 25^{\circ}C$					
Parameter	Symbol	Rating	Unit		
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V		
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	40	V		
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	v		
Collector current	I <sub>C</sub>	1.5	А		
Peak collector current	I <sub>CP</sub>	3	А		
Collector power dissipation	P <sub>C</sub>	10	W 🔬		
Junction temperature	Tj	150	°C		
Storage temperature	T <sub>stg</sub>	-55 to +150	°C		





Note) Self-supported type package is also prepared.

#### Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

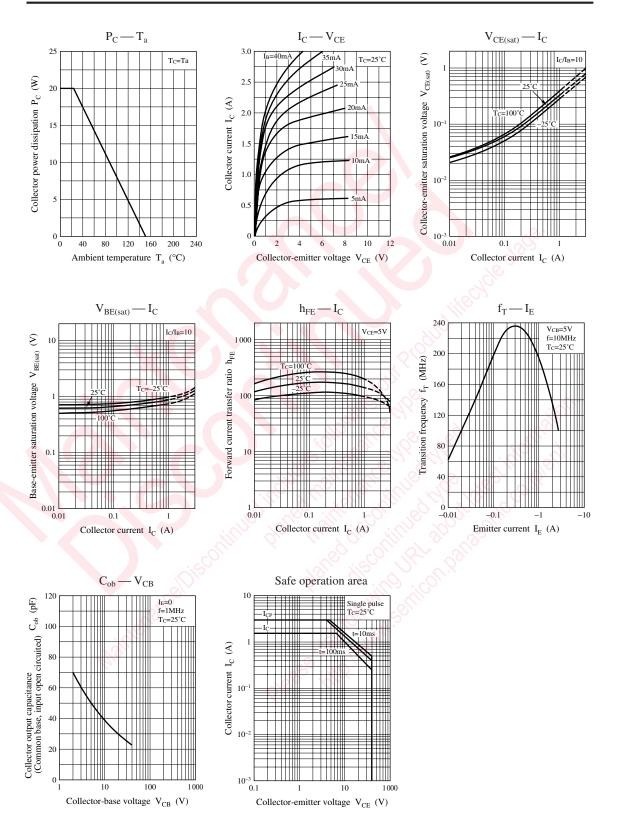
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emiter open)	V <sub>CBO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm E} = 0$	50	0		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	40			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 20 V, I_E = 0$			1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}, I_B = 0$			100	μΑ
Emiter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 5 V, I_C = 0$			10	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 5 V, I_C = 1 A$	80		220	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 0.15 \text{ A}$			1	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 2$ A, $I_{\rm B} = 0.2$ A			1.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 5 \text{ V}, I_{C} = -0.5 \text{ A}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		35		pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

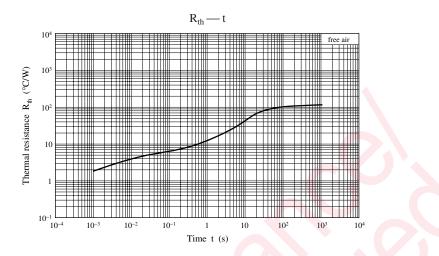
2. \*: Rank classification

Rank	R	S
$h_{\rm FE}$	80 to 160	120 to 220

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